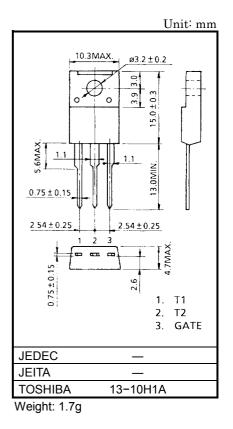
TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM10LZ47

AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage : V_{DRM} = 800V
- R.M.S. On–State Current : I_T (RMS) = 10A
- High Commutation (dv / dt)
- Isolation Voltage
- : $V_{ISOL} = 1500 V AC$
- MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage	V _{DRM}	800	V	
R.M.S On-State Current (Full Sine Waveform)	I _{T (RMS)}	10	А	
Peak One Cycle Surge On-State	l=	100 (50Hz)	А	
Current (Non-Repetitive)	ITSM	110 (60Hz)	~	
I ² t Limit Value	l ² t	50	A ² s	
Critical Rate of Rise of On-State Current (Note)	di / dt	50	A / µs	
Peak Gate Power Dissipation	P _{GM}	5	W	
Average Gate Power Dissipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage	V _{FGM}	10	V	
Peak Gate Current	I _{GM}	2	А	
Junction Temperature	Tj	-40~125	°C	
Storage Temperature Range	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t = 1min.)	VISOL	1500	V	



Note: di / dt test condition $V_{DRM} = 0.5 \times \text{Rated}, I_{TM} \le 15\text{A}, t_{dW} \ge 10\mu\text{s},$

 $t_{gr} \le 250$ ns, $i_{gp} = I_{GT} \times 2.0$

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC SYMBOL TEST COND		CONDITION	MIN	TYP.	MAX	UNIT		
Repetitive Peak Off-State Current I _{DRM}		I _{DRM}	V _{DRM} = Rated		_	—	20	μA
Gate Trigger Voltage	Ι	V _{GT}	V _D = 12V, R _L = 20Ω	T2 (+) , Gate (+)		_	1.5	V
	П			T2 (+) , Gate (−)	_	_	1.5	
	III			T2 (-) , Gate (-)		_	1.5	
Gate Trigger Current	I		V _D = 12V, R _L = 20Ω	T2 (+) , Gate (+)		—	30	mA
	Ш	I _{GT}		T2 (+) , Gate (-)		_	30	
	III			T2 (-) , Gate (-)		_	30	
Peak On-State Voltage		V _{TM}	I _{TM} = 15A			_	1.5	V
Gate Non-Trigger Voltage		V _{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V
Holding Current		Ι _Η	V _D = 12V, I _{TM} = 1A			_	50	mA
Thermal Resistance		R _{th (j−c)}	Junction to Case, AC			_	3.4	°C/W
Critical Rate of Rise of Off-State Voltage		dv / dt	V _{DRM} = 600V, T _j = 125°C Exponential Rise		_	300	_	V / µs
Critical Rate of Rise of Off-State Voltage at Commutation		(dv / dt) c	V _{DRM} = 400V, T _j = 125°C (di / dt) c = - 5.5A / ms		10	_	_	V / µs

MARKING

	NUMBER	SYMBOL		MARK
	*1	TOSHIBA PRODUCT MARK		5
	*2	TYPE	SM10LZ47	M10LZ47
	*3		arting from phabet A t Decimal Digit he Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998

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